WHAT IS CLAIMED IS:

1. A semiconductor laser device comprising:

a laser emission part for emitting a laser beam;

a laser reception part for receiving a backward beam of the laser beam reflected by an irradiation object;

a polarization hologram for transmitting the laser beam directed from the laser emission part to the irradiation object as a forward beam without diffracting the beam, and diffracting a backward beam of the laser beam, which is a return beam of the forward beam that has been reflected by the irradiation object, so that the backward beam is deflected from a direction directed toward the laser emission part and further directed toward the laser reception part; and

a three-beam diffraction grating for dividing a holographic diffracted beam, which results from the diffraction of the backward beam by the polarization hologram, into three beams and for letting the beam incident on the laser reception part.

2. The semiconductor laser device according to Claim 1, wherein

the polarization hologram and the three-beam diffraction grating are integrated together.

3. The semiconductor laser device according to Claim 1, wherein

the three-beam diffraction grating is so positioned that the forward beam directed from the laser emission part toward the irradiation object is inhibited from being incident on the three-beam diffraction grating.

4. The semiconductor laser device according to Claim 1, wherein

the laser reception part includes a first photoreception part for receiving a +1st-order diffracted beam derived from the polarization hologram, and a second photoreception part for receiving a -1st-order diffracted beam derived from the polarization hologram.

5. The semiconductor laser device according to Claim 1, wherein

the three-beam diffraction grating varies in diffraction efficiency depending on positions in a grating-extension direction along which the grating extends.

6. The semiconductor laser device according to Claim 5, wherein

in the three-beam diffraction grating, a land width to groove width ratio of land portions and groove

portions which constitute the grating continuously varies along the grating-extension direction.

7. The semiconductor laser device according to Claim 5, wherein

in the three-beam diffraction grating, groove depth of the grating continuously varies along the grating-extension direction.

8. The semiconductor laser device according to Claim 5, wherein

in the three-beam diffraction grating, groove depth of the grating varies stepwise along the grating-extension direction.

9. An optical pickup device comprising:

a laser emission part for outputting a laser beam;

a laser reception part for receiving a backward beam of the laser beam reflected by an optical disk;

a polarization hologram for transmitting the laser beam directed from the laser emission part to the optical disk as a forward beam without diffracting the beam, and diffracting a backward beam of the laser beam, which is a return beam of the forward beam that has been

reflected by the optical disk, so that the backward beam is deflected from a direction directed toward the laser emission part and further directed toward the laser reception part;

a 1/4 wave plate corresponding to a wavelength of the laser beam

an objective lens for focusing the laser beam onto the optical disk; and

a three-beam diffraction grating for dividing a holographic diffracted beam, which results from the diffraction of the backward beam by the polarization hologram, into three beams and for letting the beam incident on the laser reception part.